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NTE56 Silicon NPN Transistor High Gain Switch and Pass Regulator

Absolute Maximum Ratings: ($T_A = +25^\circ\text{C}$ unless otherwise specified)

Collector-Emitter Voltage, V_{CEO}	80V
Collector-Base Voltage, V_{CBO}	100V
Emitter-Base Voltage, V_{EBO}	6V
Collector Current, I_C	3A
Base Current, I_B	1A
Collector Power Dissipation ($T_C = +25^\circ\text{C}$), P_D	25W
Junction Temperature, T_J	+150°C
Storage Temperature Range, T_{stg}	-55° to +150°C

Electrical Characteristics: ($T_A = +25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cutoff Current	I_{CBO}	$V_{CB} = 100V$	-	-	10	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB} = 6V$	-	-	100	μA
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = 25\text{mA}$	80	-	-	V
DC Current Gain	h_{FE}	$V_{CE} = 4V, I_C = 0.5A$	500	-	-	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 2A, I_B = 50\text{mA}$	-	-	0.5	V
Current Gain-Bandwidth Product	f_T	$V_{CE} = 12V, I_E = -0.2A$	-	15	-	MHz
Capacitance	C_{OB}	$V_{CB} = 10V, f = 1\text{MHz}$	-	50	-	pF

